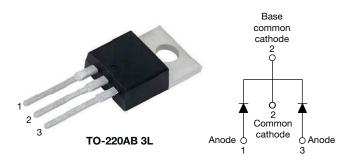
**Vishay Semiconductors** 

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# Ultrafast Rectifier, 10 A FRED Pt<sup>®</sup>



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 2 x 5 A						
V <sub>R</sub>	200 V					
V <sub>F</sub> at I <sub>F</sub>	0.87 V					
t <sub>rr</sub> typ.	See Recovery table					
T <sub>J</sub> max.	175 °C					
Package	TO-220AB 3L					
Circuit configuration	Common cathode					

### **FEATURES**

- · Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Designed and gualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V			
Average restified forward ourrest	per leg	I		5				
Average rectified forward current	total device	IF(AV)	Rated V <sub>R</sub> , T <sub>C</sub> = 149 °C	10				
Non-repetitive peak surge current p	er leg	I <sub>FSM</sub>		50	А			
Peak repetitive forward current per leg		I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz $T_{C} = 149 \text{ °C}$	10				
Operating junction and storage temp	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS PER LEG</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	ETER SYMBOL TEST CONDITIONS					UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage V <sub>F</sub>		I <sub>F</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.87	0.99	V	
	V <sub>F</sub>	I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	1.02	1.20		
		I <sub>F</sub> = 10 A	-	1.12	1.25		
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	10		
neverse leakage current	I <sub>R</sub>	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	8	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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DYNAMIC RECOVERY CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	50 A/µs, V <sub>R</sub> = 30 V	-	-	35			
Reverse recovery time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$		-	-	25	ns		
neverse recovery time		T <sub>J</sub> = 25 °C		-	24	-			
		T <sub>J</sub> = 125 °C		-	35	-			
Dook rooovon, ourront		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 5 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 160 V	-	3.3	-	А		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	5.0	-	~		
	0	T <sub>J</sub> = 25 °C		-	33	-	nC		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	76	-	nC		

THERMAL MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	5		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	-	
Weight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB 3L		MUR1	020CT		

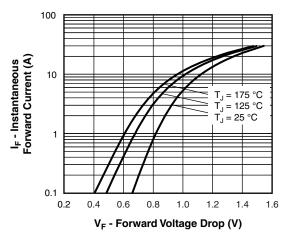


Fig. 1 - Typical Forward Voltage Drop Characteristics

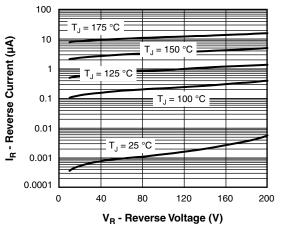


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

### **VS-MUR1020CT-M3**

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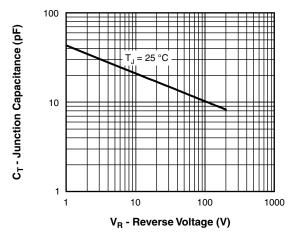


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

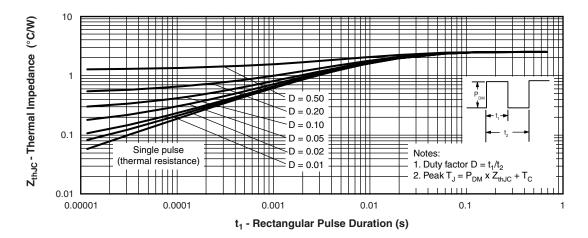
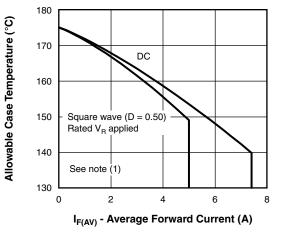
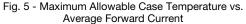


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

Average Power Loss (W)





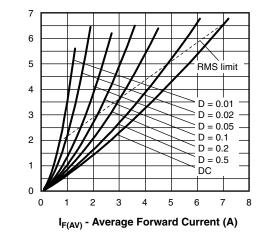


Fig. 6 - Forward Power Loss Characteristics

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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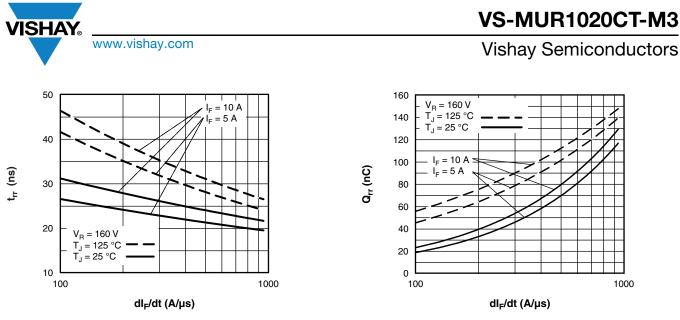


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

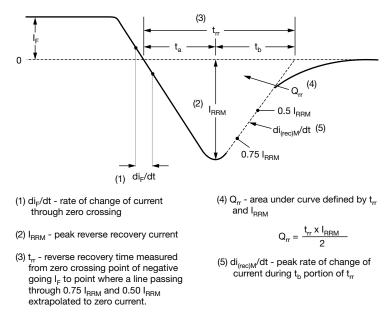


Fig. 9 - Reverse Recovery Waveform and Definitions

## VS-MUR1020CT-M3

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#### **ORDERING INFORMATION TABLE**

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Device code	VS-	MUR	10	20	СТ	-M3
	1	2	3	(4)	5	6
	<b>1</b>	- Visł	av Sem	nicondua	ctors pr	oduct
	2		,	UR serie		
	3	- Cur	rent rati	ng (10 =	= 10 A)	
	4	- Volt	age rati	ng (20 =	= 200 V)	
	5	- CT	= cente	r tap (dı	ual) 3L T	0-220/
	6	- Env	ironmer	ntal digit	:	
		-M3	= halog	gen-free	e, RoHS	-compli

ORDERING INFORMATION (Example)						
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION						
VS-MUR1020CT-M3	50	Antistatic plastic tubes				

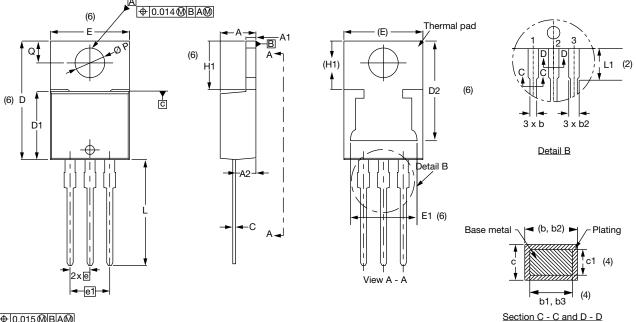
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



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## **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches



#### ⊕0.015@BA@



Γ		
F		-

SYMBOL	MILLIMETERS INCHES		NOTES		
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

SYMBOL	MILLIN	IETERS	INC	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Conforms to JEDEC<sup>®</sup> outline TO-220AB

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

<sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only

- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

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 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994  $\,$ 

<sup>&</sup>lt;sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>&</sup>lt;sup>(5)</sup> Controlling dimensions: inches



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